

长春新产业光电技术有限公司

Changchun New Industries Optoelectronics Tech. Co., Ltd.

DATA SHEET

EO-532-Subnano-Hi/1~2000μJ/1~10W

HIGH ENERGY DIODE PUMPED ALL-SOLID-STATE Q-SWITCHED LASER

High energy diode pumped all solid state Q-switched laser at 532nm has the features of high single pulse energy, short pulse duration, and high peak power, which is widely used in laser engraving, non-linear optics, scientific research, OPO and so on.







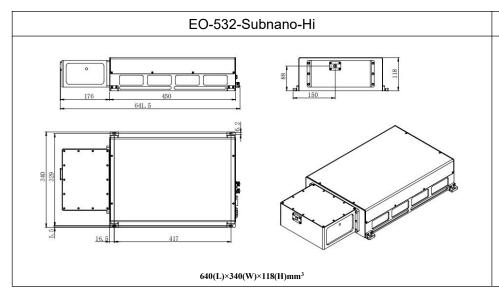


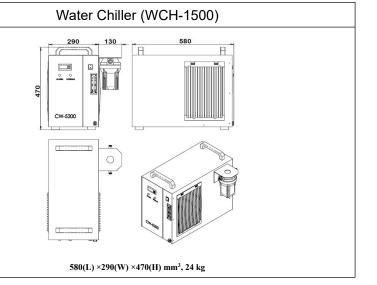
SPECIFICATIONS

Wavelength (nm)	532±1nm	
Operating mode	Q-switched: EO (Electro-optic)	
Single pulse energy (uJ)	1000uJ@5KHz	2000uJ@5KHz
Output power (W)	5	10
Power stability	<5%, <3%, <2%	
Pulse duration (ns)	<1.5ns@5KHz	1.5~2ns@5KHz
Rep. rate (kHz)	100Hz~10kHz (Customized)	
Beam diameter (mm)	~1.2mm	~1.5mm
Beam divergence, full angle (mrad)	<3mrad	
Cooled method	Air cooled@<2kHz; Water cooled@>2kHz	
Warm-up time (minutes)	<15	
Power supply	DC 24V	
Operating temperature (°C)	15~30	
Expected lifetime (hours)	10000h	
Warranty period	1 year	











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